

## ABSTRACT

Provided is a mask blank in which a thin film for transfer pattern formation is provided on a main surface of a transparent substrate. The thin film is made of a material containing a transition metal and silicon and further containing at least one of oxygen and nitrogen. The thin film has as its surface layer an oxide layer with an oxygen content higher than that of the thin film of a region other than the surface layer. The thin film is formed so that the thickness of its outer peripheral portion is greater than that of its central portion on the main surface side. The oxide layer is formed so that the thickness of its outer peripheral portion is greater than that of its central portion on the main surface side.